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Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	10/623794
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811 2823
Examiner Name	Unknown Michelle Estrada

Sheet 1 of 11

Attorney Docket No: 1303.108US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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	Examiner Name	Unknown-M: Estrada
Sheet 2 of 11		Attorney Docket No: 1303.108US1

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	Group Art Unit	2811-2823
	Examiner Name	Unknown M. Estrada
Sheet 3 of 11		Attorney Docket No: 1303.108US1

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	Application Number	10/623794
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	First Named Inventor	Forbes, Leonard
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	Examiner Name	Unknown M. Estrada
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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